

isc Silicon NPN Power Transistor

2SC3690

DESCRIPTION

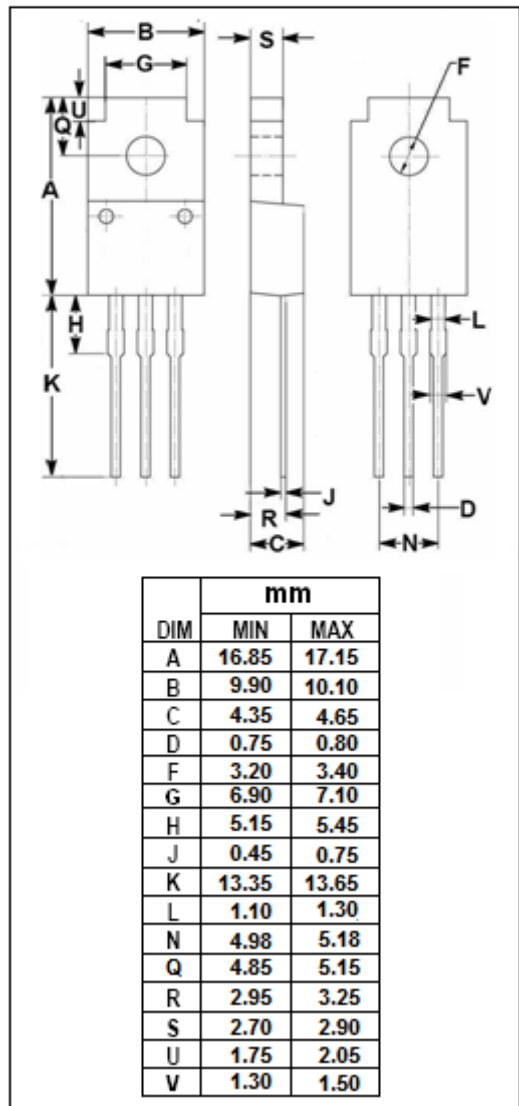
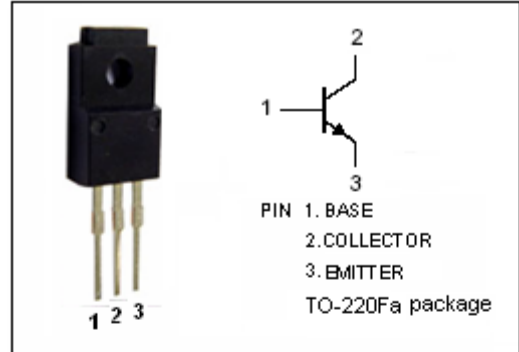
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V(\text{Max}) @ I_C = 3A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 60V (\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for high speed and power switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	6	A
I_B	Base Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	15	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC3690****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 2A; I _B = 0.2A, L= 1mH	60			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 0.1A			0.3	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.15A			0.5	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 2A; I _B = 0.1A			1.2	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 0.15A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μ A
I _{CEX}	Collector Cutoff Current	V _{CE} = 60V; V _{BE} = -1.5V T _a =125°C			10 1.0	μ A mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 0.3A; V _{CE} = 2V	100			
h _{FE-2}	DC Current Gain	I _C = 0.6A; V _{CE} = 2V	100	200	400	
h _{FE-3}	DC Current Gain	I _C = 2A; V _{CE} = 2V	60			

◆ **h_{FE-2} classifications**

M	L	K
100-200	150-300	200-400